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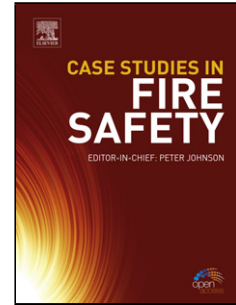
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# The effect of Sn-VO defect clustering on Zr alloy corrosion

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## Abstract

Density functional theory simulations were used to study Sn defect clusters in the oxide layer of Zr-alloys. Clustering was shown to play a key role in the accommodation of Sn in ZrO<sub>2</sub>, with the {Sn<sub>Zr</sub>:V<sub>O</sub>}<sup>×</sup> bound defect cluster dominant at all oxygen partial pressures below 10<sup>-20</sup> atm, above which Sn<sub>Zr</sub><sup>×</sup> is preferred. {Sn<sub>Zr</sub>:V<sub>O</sub>}<sup>×</sup> is predicted to increase the tetragonal phase fraction in the oxide layer, due to the elevated oxygen vacancy concentration. As corrosion progresses, the transition to Sn<sub>Zr</sub><sup>×</sup>, and resultant destabilisation of the tetragonal phase, is proposed as a possible explanation for the early first transition observed in Sn-containing Zr-Nb alloys.

*Keywords:*

Density functional theory, Zirconium, Niobium, Corrosion, Hydrogen pick-up

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## 1. Introduction

2 Since the very beginning of water cooled-reactors zirconium has been the  
3 fuel cladding material of choice because it offers the best combination of

4 neutronic, structural and corrosion properties. The first alloy regularly used  
5 in power reactors was Zircaloy-2, which contains 1.2 wt.% Sn [1, 2]. Sn was  
6 originally included as a way to mitigate the detrimental effect on corrosion  
7 associated with the N and C impurities present in the Zr-sponge, however Sn  
8 was also found to improve strength and creep resistance, and was included  
9 in the later developed Zircaloy-4 and ZIRLO alloys [1, 2, 3].

10 Modern Zr-sponge contain significantly less impurities, and it has been  
11 established that a reduction in Sn concentration improves the corrosion resis-  
12 tance of Zr-Nb alloys. For this reason it has been removed from many alloys  
13 such as M5 [4]. The role of Sn in corrosion is still poorly understood, however  
14 work performed by Wei *et al.* [5] has shown that Sn does not influence the cor-  
15 rosion kinetics of Zr-Nb alloys, but rather that the removal of Sn delays the  
16 onset of transition. This behaviour does seem to be limited to Zr-Nb alloys  
17 as Ortner *et al.* [6] did not observe this behaviour in a study of Zircaloy-4 and  
18 it is noted that Zr-Nb-Sn alloys seem to behave quite differently to the Zir-  
19 caloy series of alloys. Further, X-ray diffraction (XRD) measurements have  
20 shown that the tetragonal  $ZrO_2$  phase fraction increases with increasing Sn  
21 content in Nb containing alloys [5]. Garner *et al.* suggested that Sn incorpo-  
22 rated into the oxide may therefore be one of the stabilising features of this  
23 oxide phase; other contributions are from the compressive stress, generated  
24 on transformation of metal to oxide, and the possibly very small (nano-scale)  
25 size of some tetragonal grains [7]. Recent density functional theory (DFT)  
26 studies of the role of Sn in changing the defect concentrations showed that  
27 Sn can be present in either the 2+ or 4+ charge states and that there was a  
28 critical oxygen partial pressure at which point  $Sn^{2+}$ , present at low oxygen

29 partial pressures, would switch to  $\text{Sn}^{4+}$  in the oxide layer [8]. Hulme *et al.*  
30 used X-ray absorption near edge spectroscopy (XANES) to prove that  $\text{Sn}^{2+}$   
31 did indeed exist in the oxide layer but were not able to determine any depth  
32 profile for the 2+/4+ charge states for Sn [9]. It was postulated in both  
33 papers that  $\text{Sn}^{2+}$  may have created charged oxygen vacancies to charge ba-  
34 lance the  $\text{Sn}^{2+}$  cations and the presence of these oxygen vacancies in turn  
35 stabilised the tetragonal phase. As the oxide layer thickens and the oxygen  
36 partial pressure increases (i.e. at a position in the oxide that is further from  
37 the metal-oxide interface) it was postulated that  $\text{Sn}^{2+}$  changes to  $\text{Sn}^{4+}$  on  
38 reaching a critical value and the vacancies were no longer needed for charge  
39 balance. This change in oxidation state of the Sn cations, and the associated  
40 drop in the oxygen vacancy concentration, destabilised the tetragonal phase  
41 and led to its transformation to the monoclinic phase and this in turn could  
42 have initiated cracking in the oxide associated with the transition because of  
43 the 4% volume increase from the tetragonal to monoclinic phases. The issue  
44 with this initial theory is it did not explain why the corrosion rate does not  
45 increase with increased oxygen vacancy concentration - something that was  
46 observed by Bell *et al.* when Zr is doped with  $\text{Sc}^{3+}$  ions [10].

47 In this paper a set of defects are modelled in tetragonal  $\text{ZrO}_2$  using the  
48 same technique employed by Bell *et al.* [8, 10, 11]. These defects are bound  
49  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}$  clusters of different configurations and charge states. It is shown  
50 that certain combinations have a strong binding energy and are favoured  
51 over the isolated Sn ion defects previously presented. The effect of non-  
52 equilibrium charge in the oxide layer is also investigated in the formulation  
53 of the Brouwer diagrams.

## 54 2. Methodology

55 DFT simulations were performed using the CASTEP 8.0 software [12],  
56 with ultra-soft pseudo potentials and a cut-off energy of 550 eV. The exchange-  
57 correlation functional was described by the Perdew, Burke and Ernzerhof  
58 (PBE) [13] formulation of the generalised gradient approximation (GGA).  
59 Integration of the Brillouin zone was performed using a Monkhorst-Pack  
60 sampling scheme [14], with a minimum k-point separation of  $0.045 \text{ \AA}^{-1}$ . The  
61 Pulay method [15] for density mixing was employed.

62 Self-consistent calculations were performed until an energy convergence  
63 of  $1 \times 10^{-8}$  eV between successive iterations was achieved. The convergence  
64 criteria for geometry optimisation were; a maximum difference in energy of  
65  $1 \times 10^{-5}$  eV, an atomic displacement of  $5 \times 10^{-4}$  Å between iterations and a  
66 maximum force between ions of  $1 \times 10^{-2}$  eV/Å.

67 Non-defective 108 atom t-ZrO<sub>2</sub> and 96 atom m-ZrO<sub>2</sub> supercells were ge-  
68 ometry optimised under constant (zero) pressure, from which all defective  
69 structures were subsequently generated and the energy minimised under con-  
70 stant volume. An energy correction calculated using the screened Madelung  
71 method [16] was used to account for the electrostatic self-interaction of de-  
72 fects created by the use of periodic conditions and a finite supercell size using  
73 dielectric values calculated by Zhao and Vanderbilt [17].

74 Each single and clustered defect in each overall charge state of interest  
75 was simulated in isolation in a supercell of the requisite ZrO<sub>2</sub> phase. Defect  
76 clusters consisting of a substitutional Sn atom, Sn<sub>Zr</sub>, and an oxygen vacancy,  
77 V<sub>O</sub>, (i.e. {Sn<sub>Zr</sub>:V<sub>O</sub>}) were prepared by removing the nearest O ion to the Sn<sub>Zr</sub>  
78 defect. The overall charge on the cluster was varied from -2 to +2 so that the

79 Sn ion is able to assume a range of possible oxidation states. Defect formation  
 80 energies ( $E^f$ ) were calculated for each defect simulated using the methodology  
 81 outlined in [8]. The calculated formation energies for each isolated defect  
 82 were then used to approximate the interactions between multiple defects, as  
 83 would be expected in a real oxide layer.

84 In any given defective cell, the sum of all defects multiplied by their charge  
 85 must equal zero, since there is no overall charge on the crystal. This can be  
 86 expressed as follows:

$$\sum_i q_i c_i - N_c \exp\left(-\frac{E_g - \mu_e}{k_B T}\right) + N_v \exp\left(-\frac{\mu_e}{k_B T}\right) = 0 \quad (1)$$

87 where the first term is the sum of the charges of all ionic defects ( $q_i$  is the  
 88 ionic charge and  $c_i$  the concentration of ionic defect  $i$ ), the second term is  
 89 the electron concentration and the third term the hole concentration in the  
 90 crystal.  $N_c$  and  $N_v$  are the density of states for the conduction and valence  
 91 bands,  $E_g$  is the band gap of the crystal,  $\mu_e$  is the electron chemical potential,  
 92  $k_B$  is the Boltzmann constant and  $T$  the temperature. The concentrations  
 93  $c_i$  of each ionic defect  $i$  are calculated using the approach developed by Ka-  
 94 samatsu *et al.* [18], which uses standard Boltzmann statistics to calculate  
 95 concentrations but also accounts for ionic defects competing for the same  
 96 lattice site.

97 Tetragonal  $\text{ZrO}_2$  is a wide band gap insulator, and as such the concentra-  
 98 tions of electrons and holes are expected to be sufficiently low that Boltzmann  
 99 statistics are appropriate. Self-trapping of electrons causes a reduction in the  
 100 formation energy of electrons in the conduction band, when compared to the  
 101 value calculated by  $E_g - \mu_e$ , however due to the wide band gap the difference

102 in energy is minimal and so this is an acceptable approximation [19].

103 Using the relationship in Equation 1, the electron chemical potential re-  
104 quired to ensure charge neutrality for a given set of chemical potentials and  
105 oxygen partial pressure, and thus the concentration of all defects ( $[D]$ ), can  
106 be calculated. The chemical potentials of the reactive species were obtained  
107 from formation energies of the relevant oxides following established met-  
108 hods [8, 19, 20, 21, 22]. The predicted defect concentrations as a function of  
109 oxygen partial pressure were then plotted for each oxide to produce Brouwer  
110 diagrams. As oxygen partial pressure in the oxide layer decreases with dis-  
111 tance from the oxide/water interface, a Brouwer diagram can provide insight  
112 into the defect concentrations through the thickness of the oxide. For all  
113 diagrams, the DFT predicted band gaps of 3.40 eV for the monoclinic phase  
114 and 3.95 eV for the tetragonal phase were used.

115 The approach used in this work follows the methodology outlined in pre-  
116 vious work by Bell *et al.* [8, 10, 11].

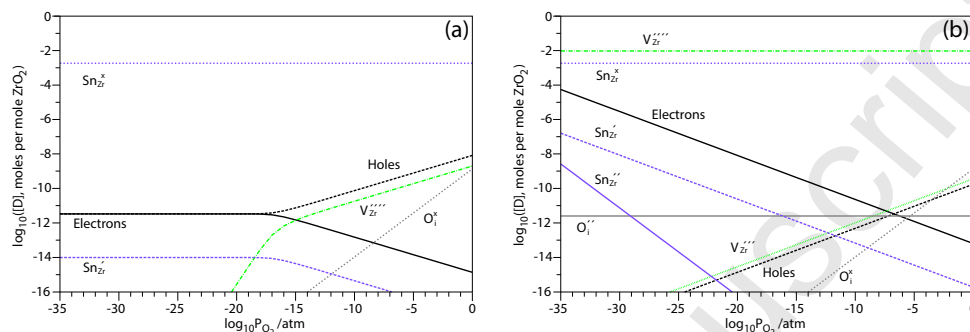
117 **3. Results and Discussion**

Figure 1: Brouwer diagrams showing the predicted defect concentrations (plotted as the log of the concentration, in units of moles per mole of  $\text{ZrO}_2$ ) in monoclinic  $\text{ZrO}_2$  at 635 K doped with Sn at a concentration of  $1 \times 10^{-3}$  moles per mole of  $\text{ZrO}_2$ . The behaviour of the Sn dopant under equilibrium conditions is shown in (a). In (b) a space charge of 0.2 (moles of  $e^-$  per mole of  $\text{ZrO}_2$ ) has been applied in order to investigate the behaviour under non-equilibrium charge conditions.

118 Figure 1 shows the predicted defect behaviour for monoclinic  $\text{ZrO}_2$  do-  
 119 ped with Sn at a concentration of  $1 \times 10^{-3}$  moles per mole  $\text{ZrO}_2$ . This Sn  
 120 concentration, while lower than what would generally be expected for the  
 121 oxide layer, was chosen to be sure that the solubility limit in the oxide phase  
 122 was not exceeded. Across all oxygen partial pressures and despite the appli-  
 123 cation of a high concentration of non-equilibrium charge to the system (see  
 124 Figure 1b),  $\text{Sn}_{\text{Zr}}^{\times}$  is predicted to be the dominant defect type. This suggests  
 125 that regardless of the local conditions, Sn in monoclinic  $\text{ZrO}_2$  should only be  
 126 observed in the 4+ oxidation state.



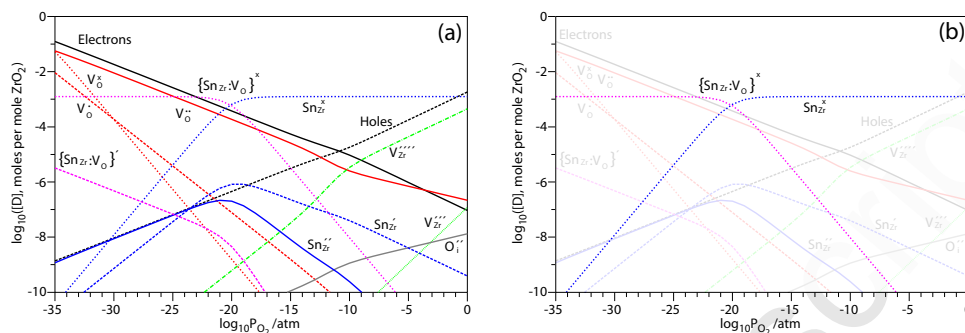


Figure 2: Brouwer diagrams showing the predicted defect concentrations in tetragonal  $\text{ZrO}_2$  at 1500 K, doped with Sn at a concentration of  $1 \times 10^{-3}$  moles per mole of  $\text{ZrO}_2$ .  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}$  clusters were simulated, and included in the diagrams as an alternative Sn defect type, with the overall Sn concentration remaining fixed. Both diagrams display the same data, however due to the complexity of the diagrams, the intrinsic and non-dominant Sn defects are partially obscured in (b) to allow the clear observation of the important Sn behaviour.

127 Previous work, investigating the behaviour of Sn in tetragonal  $\text{ZrO}_2$ , sug-  
 128 gested that Sn can exist in both 2+ and 4+ oxidation states in the tetragonal  
 129 phase and that the influence of oxygen vacancies could be significant [8]. Fi-  
 130 gure 2 suggests that while  $\text{Sn}_{\text{Zr}}^{\times}$  remains the dominant Sn defect at high oxy-  
 131 gen partial pressures, below  $10^{-20}$  atm the  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  bound defect cluster is  
 132 favoured (note: other clusters such as  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\prime}$  that incorporate  $\text{Sn}^{3+}$  were  
 133 considered, but are predicted to be of negligible concentration). The binding  
 134 energy of  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  was calculated to be 1.68 eV, indicative of a strong  
 135 energetic preference to form a cluster.  $\text{Sn}_{\text{Zr}}^{\prime\prime}$  has a calculated defect volume  
 136 of  $44.22 \text{ \AA}^3$ , this is very large and causes a calculated stress of 6.04 GPa on  
 137 the 108 atom simulation supercell. Conversely  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  has a calculated  
 138 defect volume of  $5.43 \text{ \AA}^3$ , only slightly larger than that of  $\text{Sn}_{\text{Zr}}^{\times}$  ( $2.02 \text{ \AA}^3$ ), sug-

139 gesting that the cluster may form in preference to isolated defects in order  
140 to reduce lattice stress.

141 Corrosion of Zr metal is known to occur close to the metal/oxide inter-  
142 face (i.e. oxygen diffuses through the oxide layer to the metal, rather than Zr  
143 ions diffusing outwards towards the environment), so the Zr-metal is oxidised  
144 under a low oxygen partial pressure; conditions similar to those on the left  
145 hand side of the diagrams in Figure 2. Thus, as oxidation occurs the Sn ions  
146 have a strong preference to oxidise to the 2+ state and bind with an oxygen  
147 vacancy to form a  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  cluster. As corrosion progresses, the metal  
148 oxide interface moves deeper into the Zr-metal and the oxygen partial pres-  
149 sure in the previously formed  $\text{ZrO}_2$  gradually increases. In an intrinsic oxide  
150 layer, this would lead to a gradual reduction in the oxygen vacancy concen-  
151 tration, however as shown in Figure 2 the  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  clusters remain at a  
152 relatively constant concentration at oxygen partial pressures below  $10^{-23}$  atm.  
153 The presence of the Sn ions, therefore, results in an increased oxygen vacancy  
154 concentration in the tetragonal phase of the oxide layer. Since oxygen va-  
155 cancies are known to stabilise the tetragonal phase of  $\text{ZrO}_2$ , the presence of  
156 Sn in the oxide layer results in an increased tetragonal phase fraction. This  
157 result agrees well with XRD work [5], which reported that as the Sn content  
158 of ZIRLO was reduced, the measured tetragonal phase fraction also reduced.

159 As discussed in the introduction, previous work suggested that an increa-  
160 sed oxygen vacancy concentration may lead to an increased tetragonal phase  
161 fraction in Zr-based alloys. However, what has not previously been discussed  
162 is why the increased oxygen vacancy concentration in Sn-containing Zr alloys  
163 does not lead to an elevated corrosion rate, as is observed in other similar sy-

164 stems (for example,  $\text{Sc}^{3+}$  dramatically increases both the oxygen vacancy  
 165 concentration and the corrosion rate in Zr-based alloys [10]). As shown in  
 166 Figure 3, the pre-transition corrosion rate does not appear to be influenced  
 167 at all by the Sn content of the alloy, rather the increased long-term corrosion  
 168 behaviour observed in Sn-containing alloys appears to be due to an earlier  
 169 transition occurring in high Sn alloys.

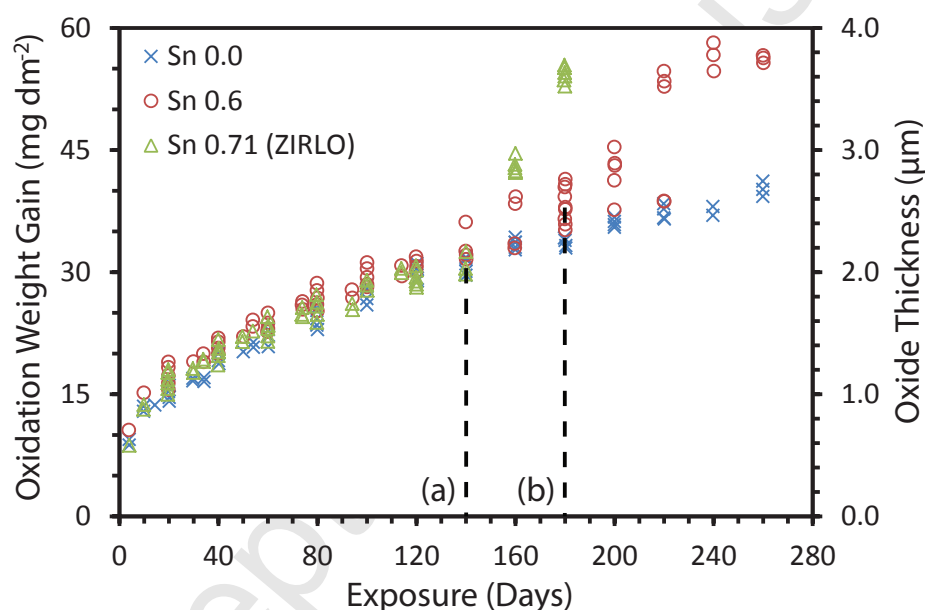


Figure 3: Oxide weight gain results showing no change in pre-transition corrosion rate but an earlier first transition in Sn-containing Zr alloys containing: 0.71 (ZIRLO), 0.51 and 0.01 at.% Sn. The dashed lines have been added to show the approximate point of early transition for (a) 0.71 at.% Sn (ZIRLO) after 140 days and (b) 0.51 at.% Sn after 180 days of autoclave corrosion. Corrosion was performed in an autoclave at 360 °C in simulated primary water at a saturation pressure of ~18 MPa. (Data replotted from [5]).

170 This study suggests that the additional oxygen vacancies resulting from  
 171 the inclusion of Sn in the oxide layer exist only in bound  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  clus-

172 ters and thus while the vacancy concentration, (and hence tetragonal phase  
173 fraction) is increased, the additional vacancies are assumed to have limited  
174 mobility and so do not cause a measurable increase in the corrosion rate of  
175 the alloy. As corrosion progresses, the oxygen partial pressure experienced  
176 by the Sn ions in the oxide layer increases as the metal/oxide interface moves  
177 deeper into the Zr-alloy. Once the oxygen partial pressure reaches  $10^{-20}$  atm,  
178  $\text{Sn}_{\text{Zr}}^{\times}$  becomes more energetically favourable than the  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  clusters.  
179  $\text{Sn}_{\text{Zr}}^{\times}$  does not require the presence of an oxygen vacancy for charge neutra-  
180 lity, and so the oxygen vacancy concentration in the oxide layer is reduced.  
181 Thus, the change in preferred Sn oxidation state results in tetragonal phase  
182 stabilising oxygen vacancies being removed from the lattice. This is likely to  
183 trigger a transformation of the tetragonal phase into the monoclinic phase.  
184 The tetragonal to monoclinic phase transformation is associated with a 4%  
185 increase in unit cell volume, causing buckling and cracking of the layer and  
186 potentially triggering the earlier first transition observed in Sn containing  
187 Zr-Nb alloys. As this phase transformation is driven by the presence of Sn  
188 ions in the oxide lattice, it is expected that the effect would be increasingly  
189 effective at triggering an early first transition with increasing Sn content.  
190 This agrees well with the results reproduced in Figure 3, which show that  
191 alloys containing a higher Sn content undergo increasingly early first transi-  
192 tion; 0.51 at.% Sn after approximately 180 days and 0.71 at.% Sn after 140  
193 days.

#### 194 4. Conclusions

195 1.  $\text{Sn}^{4+}$  is the dominant defect type across all oxygen partial pressures in  
196 monoclinic  $\text{ZrO}_2$ .

197 2.  $\text{Sn}^{2+}$  is dominant at low oxygen partial pressures in tetragonal  $\text{ZrO}_2$ ,  
198 transitioning to  $\text{Sn}^{4+}$  above  $10^{-20}$  atm.

199 3.  $\text{Sn}^{2+}$  forms bound  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  clusters with an oxygen vacancy, incre-  
200 asing the oxygen vacancy concentration and thus stabilising the tetragonal  
201 phase, but bound clusters prevent the increased  $\text{V}_{\text{O}}$  concentration from chan-  
202 ging the corrosion rate.

203 4. As corrosion progresses and  $\{\text{Sn}_{\text{Zr}}:\text{V}_{\text{O}}\}^{\times}$  transitions to  $\text{Sn}^{4+}$ , the additi-  
204 onal oxygen vacancies are no longer required in the system and the tetragonal  
205 phase stabilisation is lost.

206 5. The destabilised tetragonal phase transforms to monoclinic with an  
207 associated increase in volume of around 4%, possibly triggering the early  
208 oxide layer transition observed in Sn-containing Zr alloys.

209 6. The early transition triggered by the change in Sn oxidation state is  
210 expected to be more apparent with increased Sn-content.

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